

# 4V Drive Nch MOSFET

## RSJ650N10

### ● Structure

Silicon N-channel MOSFET

### ● Features

- 1) Low on-resistance.
- 2) High power package.
- 3) 4V drive.

### ● Application

Switching

### ● Packaging specifications

| Type      | Package                      | Taping |
|-----------|------------------------------|--------|
|           | Code                         | TL     |
|           | Basic ordering unit (pieces) | 1000   |
| RSJ650N10 |                              | ○      |

### ● Absolute maximum ratings (Ta = 25°C)

| Parameter                      |            | Symbol      | Limits      | Unit |
|--------------------------------|------------|-------------|-------------|------|
| Drain-source voltage           |            | $V_{DSS}$   | 100         | V    |
| Gate-source voltage            |            | $V_{GSS}$   | $\pm 20$    | V    |
| Drain current                  | Continuous | $I_D$ *3    | $\pm 65$    | A    |
|                                | Pulsed     | $I_{DP}$ *1 | $\pm 130$   | A    |
| Source current<br>(Body Diode) | Continuous | $I_S$ *3    | 65          | A    |
|                                | Pulsed     | $I_{SP}$ *1 | 130         | A    |
| Power dissipation              |            | $P_D$ *2    | 100         | W    |
| Channel temperature            |            | $T_{ch}$    | 150         | °C   |
| Range of storage temperature   |            | $T_{stg}$   | -55 to +150 | °C   |

 \*1  $P_W \leq 10\mu s$ , Duty cycle  $\leq 1\%$ 

 \*2  $T_C = 25^\circ C$ 

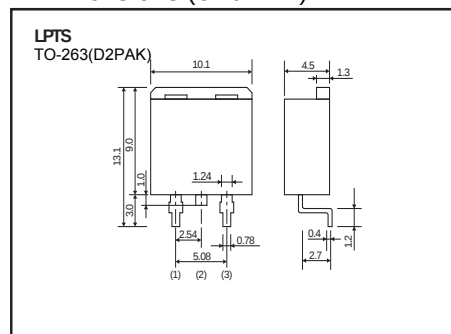
\*3 Please use within the range of SOA.

### ● Thermal resistance

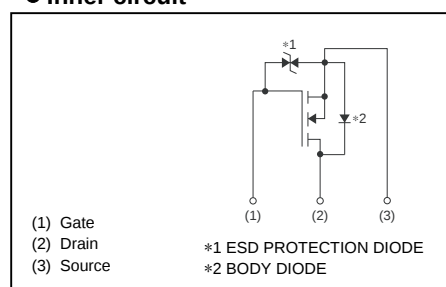
| Parameter       | Symbol           | Limits | Unit   |
|-----------------|------------------|--------|--------|
| Channel to Case | $R_{th}(ch-c)^*$ | 1.25   | °C / W |

 \*  $T_C = 25^\circ C$ 

### ● Dimensions (Unit : mm)



### ● Inner circuit



## ● Electrical characteristics (Ta = 25°C)

| Parameter                               | Symbol         | Min. | Typ.  | Max.     | Unit      | Conditions                      |
|-----------------------------------------|----------------|------|-------|----------|-----------|---------------------------------|
| Gate-source leakage                     | $I_{GSS}$      | -    | -     | $\pm 10$ | $\mu A$   | $V_{GS} = \pm 20V, V_{DS} = 0V$ |
| Drain-source breakdown voltage          | $V_{(BR)DSS}$  | 100  | -     | -        | V         | $I_D = 1mA, V_{GS} = 0V$        |
| Zero gate voltage drain current         | $I_{DSS}$      | -    | -     | 1        | $\mu A$   | $V_{DS} = 100V, V_{GS} = 0V$    |
| Gate threshold voltage                  | $V_{GS(th)}$   | 1    | -     | 2.5      | V         | $V_{DS} = 10V, I_D = 1mA$       |
| Static drain-source on-state resistance | $R_{DS(on)}^*$ | -    | 6.5   | 9.1      | $m\Omega$ | $I_D = 32.5A, V_{GS} = 10V$     |
|                                         |                | -    | 7     | 9.8      |           | $I_D = 32.5A, V_{GS} = 4V$      |
| Forward transfer admittance             | $ Y_{fs} ^*$   | 45   | -     | -        | S         | $V_{DS} = 10V, I_D = 32.5A$     |
| Input capacitance                       | $C_{iss}$      | -    | 10780 | -        | pF        | $V_{DS} = 25V$                  |
| Output capacitance                      | $C_{oss}$      | -    | 785   | -        | pF        | $V_{GS} = 0V$                   |
| Reverse transfer capacitance            | $C_{rss}$      | -    | 560   | -        | pF        | $f = 1MHz$                      |
| Turn-on delay time                      | $t_{d(on)}^*$  | -    | 45    | -        | ns        | $V_{DD} = 50V, I_D = 32.5A$     |
| Rise time                               | $t_r^*$        | -    | 170   | -        | ns        | $V_{GS} = 10V$                  |
| Turn-off delay time                     | $t_{d(off)}^*$ | -    | 640   | -        | ns        | $R_L = 1.54\Omega$              |
| Fall time                               | $t_f^*$        | -    | 480   | -        | ns        | $R_G = 10\Omega$                |
| Total gate charge                       | $Q_g^*$        | -    | 260   | -        | nC        | $V_{DD} = 50V, I_D = 32.5A$     |
| Gate-source charge                      | $Q_{gs}^*$     | -    | 24    | -        | nC        | $V_{GS} = 10V$                  |
| Gate-drain charge                       | $Q_{gd}^*$     | -    | 60    | -        | nC        |                                 |

\*Pulsed

## ● Body diode characteristics (Source-Drain)

| Parameter       | Symbol     | Min. | Typ. | Max. | Unit | Conditions               |
|-----------------|------------|------|------|------|------|--------------------------|
| Forward Voltage | $V_{SD}^*$ | -    | -    | 1.5  | V    | $I_S = 65A, V_{GS} = 0V$ |

\*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics ( I )

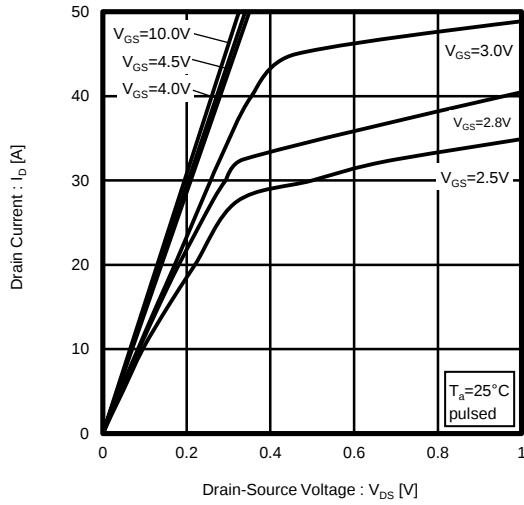


Fig.2 Typical Output Characteristics ( II )

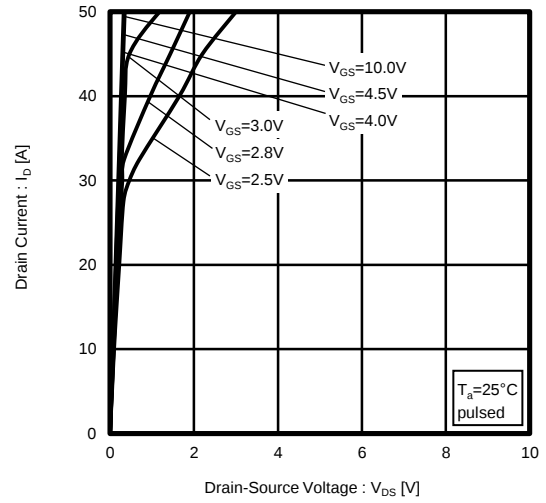


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

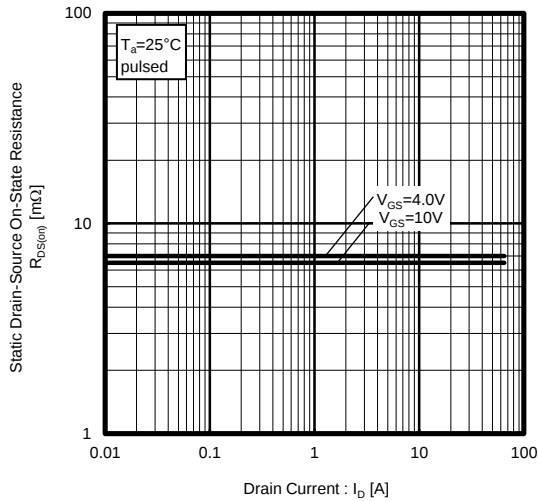


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

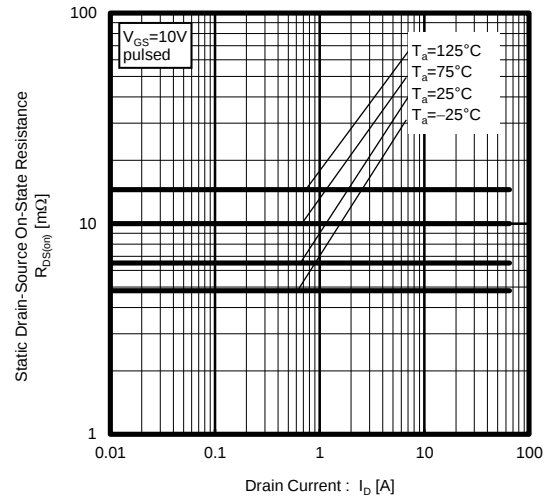


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

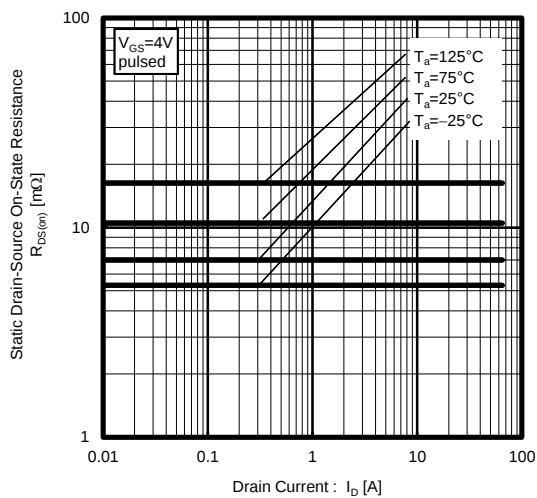


Fig.6 Forward Transfer Admittance vs. Drain Current

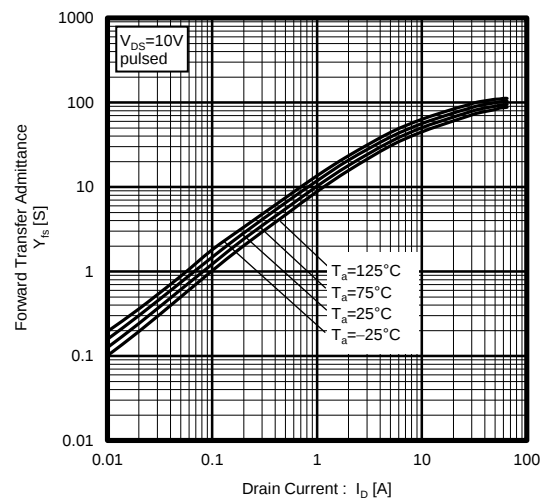


Fig.7 Typical Transfer Characteristics

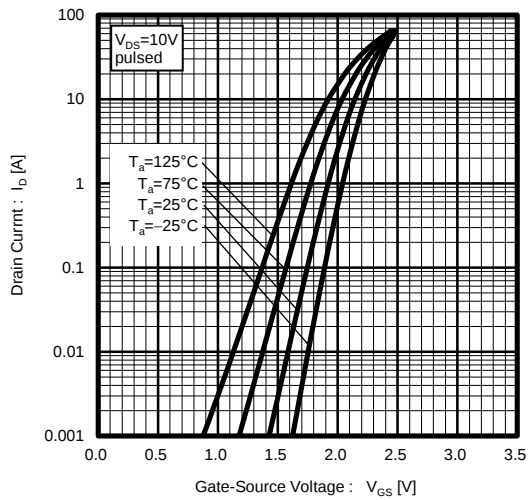


Fig.8 Source Current vs. Source-Drain Voltage

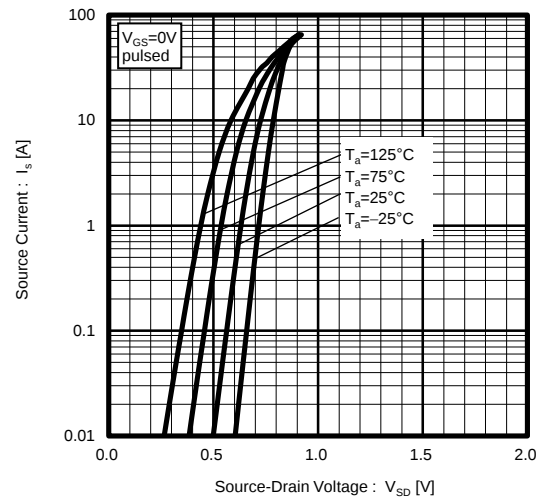


Fig.9 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

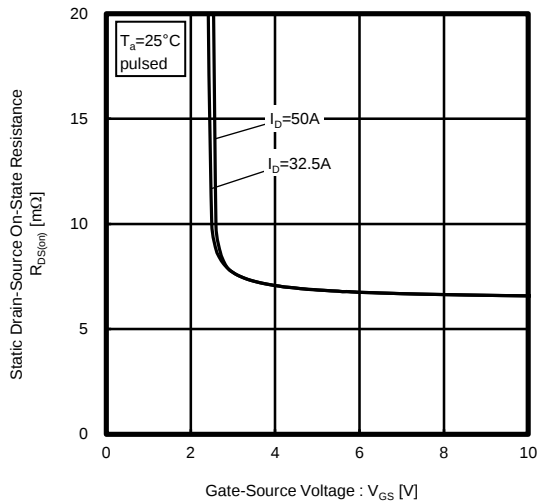


Fig.10 Switching Characteristics

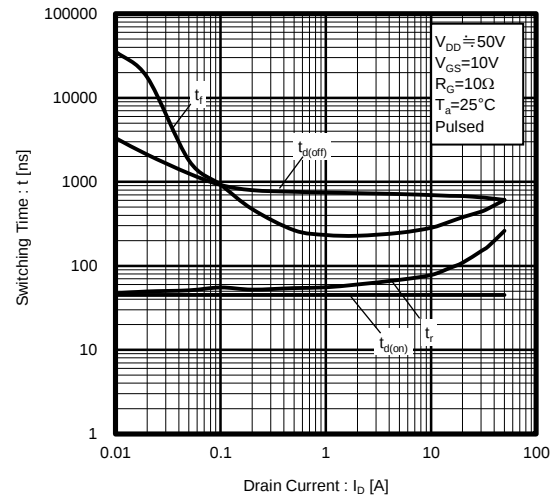


Fig.11 Dynamic Input Characteristics

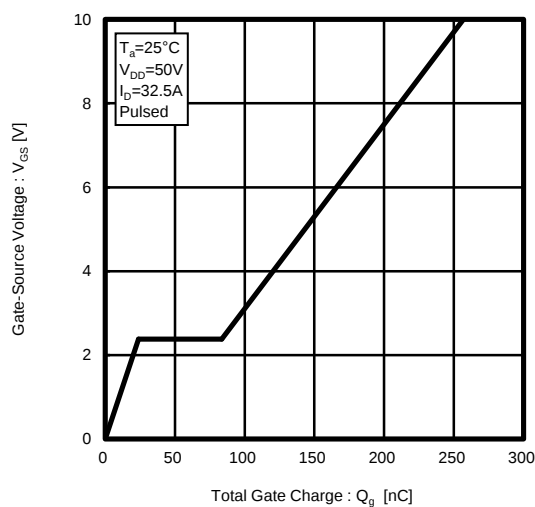


Fig.12 Typical Capacitance vs. Drain-Source Voltage

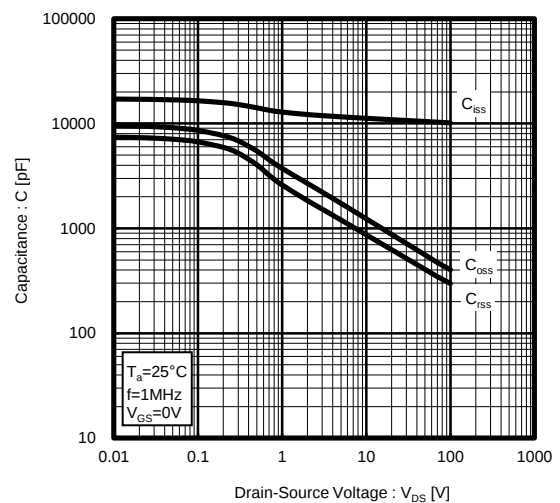


Fig.13 Normalized Transient Thermal Resistance v.s. Pulse Width

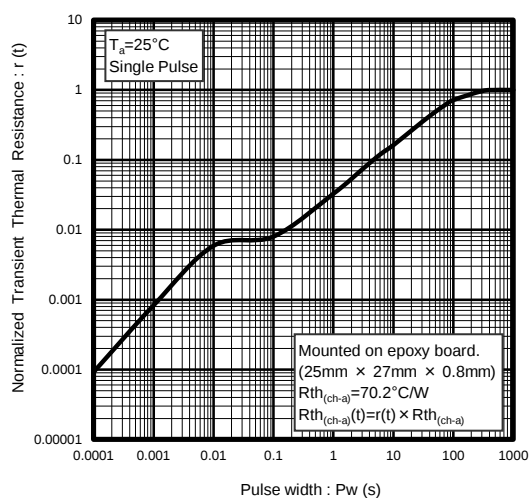
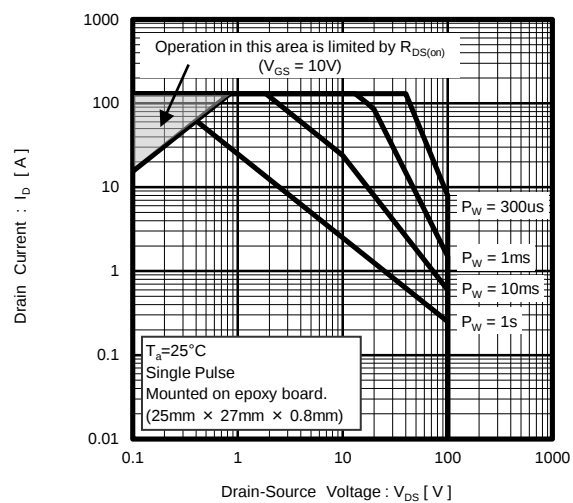


Fig.14 Maximum Safe Operating Area



# ● Measurement circuits

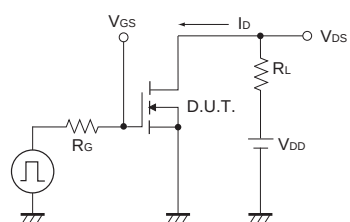


Fig.1-1 Switching Time Measurement Circuit

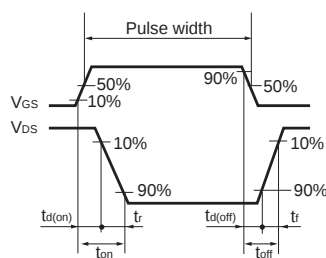


Fig.1-2 Switching Waveforms

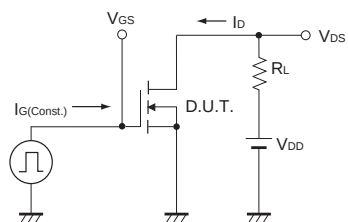


Fig.2-1 Gate Charge Measurement Circuit

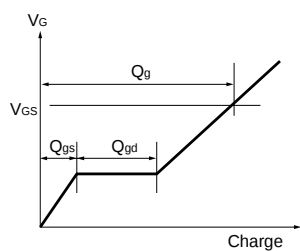


Fig.2-2 Gate Charge Waveform

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